

IN THE SPECIFICATION

Please insert before the first paragraph under BACKGROUND OF THE INVENTION of page 1 of the disclosure currently on file with the following paragraph:

This application is a Divisional of nonprovisional application serial number 09/824,225 filed April 3, 2001. Priority is claimed based on U.S. Application No. 09/824,225 filed April 3, 2001, which claims the priority of Japanese application 2000-159544 filed on May 25, 2000.

Please replace page 5, last paragraph of the Disclosure currently on file with the following paragraph:

Then, a gate insulation film 155, a gate electrode 156, and a gate side wall insulation film 157 are formed to pMODFET, and a gate insulation film 158, a gate electrode 159, and a gate side wall insulation film 160 are formed to nMOSFET (refer to FIG. 50(da)). Finally, p-type dopant is selectively ion implanted to form a source 161 and a drain 162 of pMODFET, and n-type dopant is selectively ion implanted to form a source 163 and a drain 164 of nMOSFET (refer to FIG. 50(eb)).

Please replace page 6, first paragraph of the Disclosure currently on file with the following paragraph:

Further, the result of study on the process flow in a case using a field insulation film and a device isolation insulation region is shown in FIG. 51 and FIG. 52. A field insulation film 165 in a region other than the region forming an intrinsic region for nMOSFET and pMODFET is formed on a silicon substrate 150, and a device isolation insulation film 166 is formed for isolation of the transistors (refer to FIG. 51(a)). Then, p-type and n-type dopants are ion implanted to the regions for forming nMOSFET and pMODFET, to form a p-well 151 and an n-well 152 respectively (refer to FIG. 51(b)). Then, a buffer layer 153 and a multi-layered film 154 comprising single-crystal silicon and single-crystal silicon-germanium are formed on the entire surface of the substrate by epitaxial growth. In this process, a multi-layered film of a single crystal silicon-germanium layer and a single-crystal silicon layer is formed on the silicon substrate, and a multi-layered film of a polycrystalline